

FIG. 1

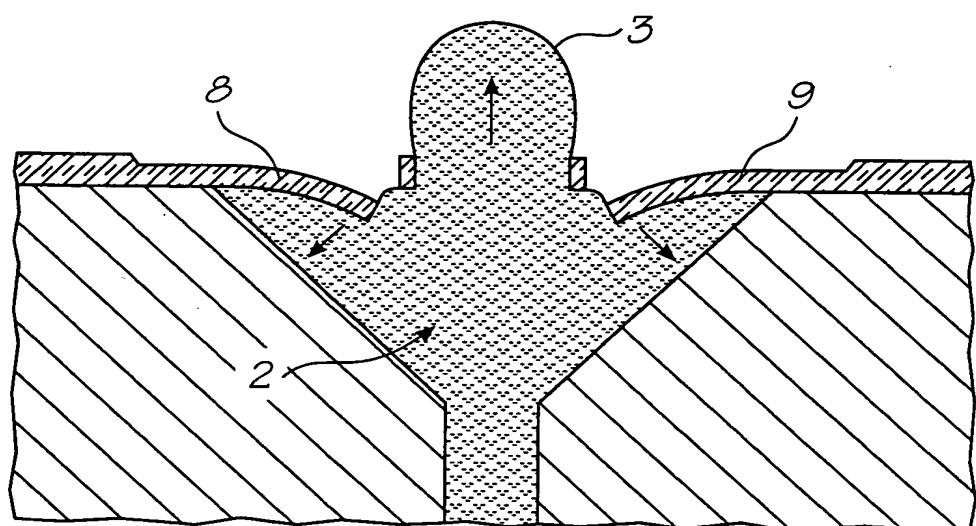


FIG. 2

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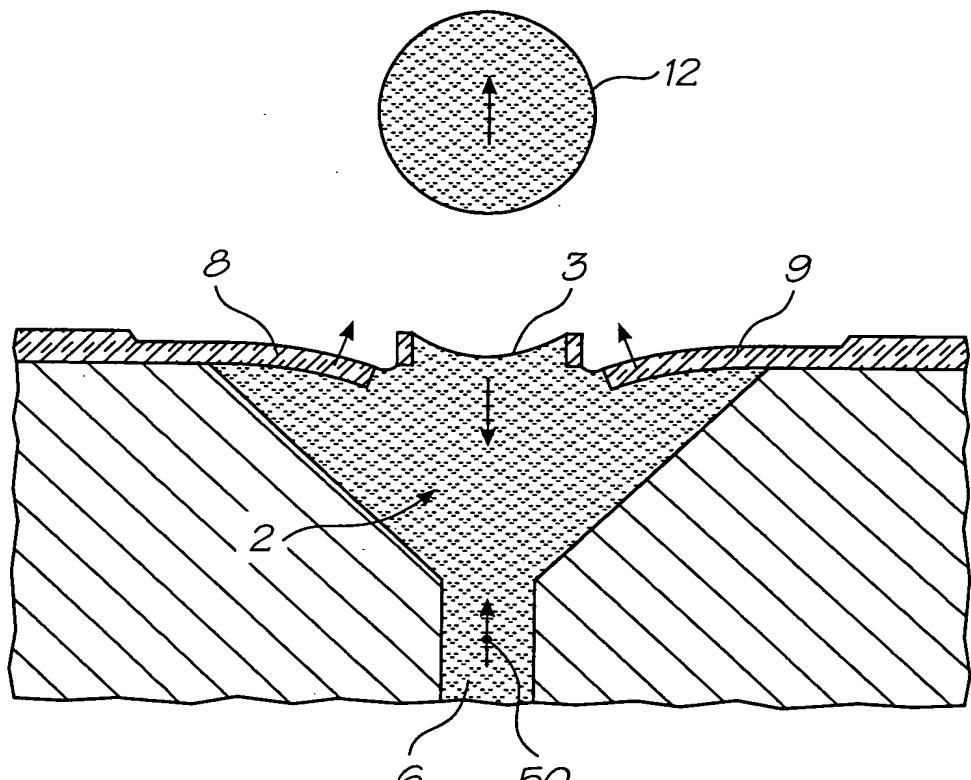


FIG. 3

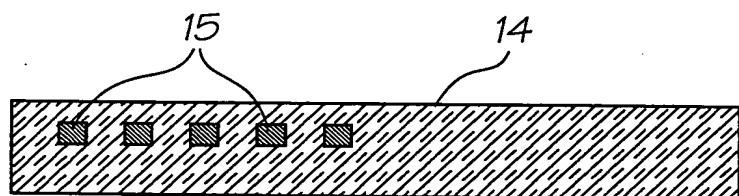


FIG. 4A

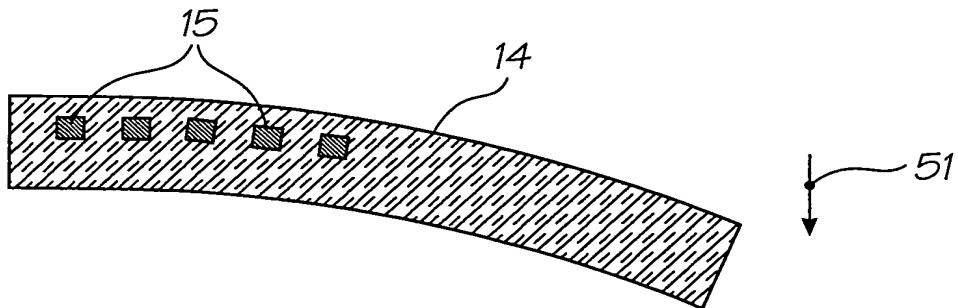
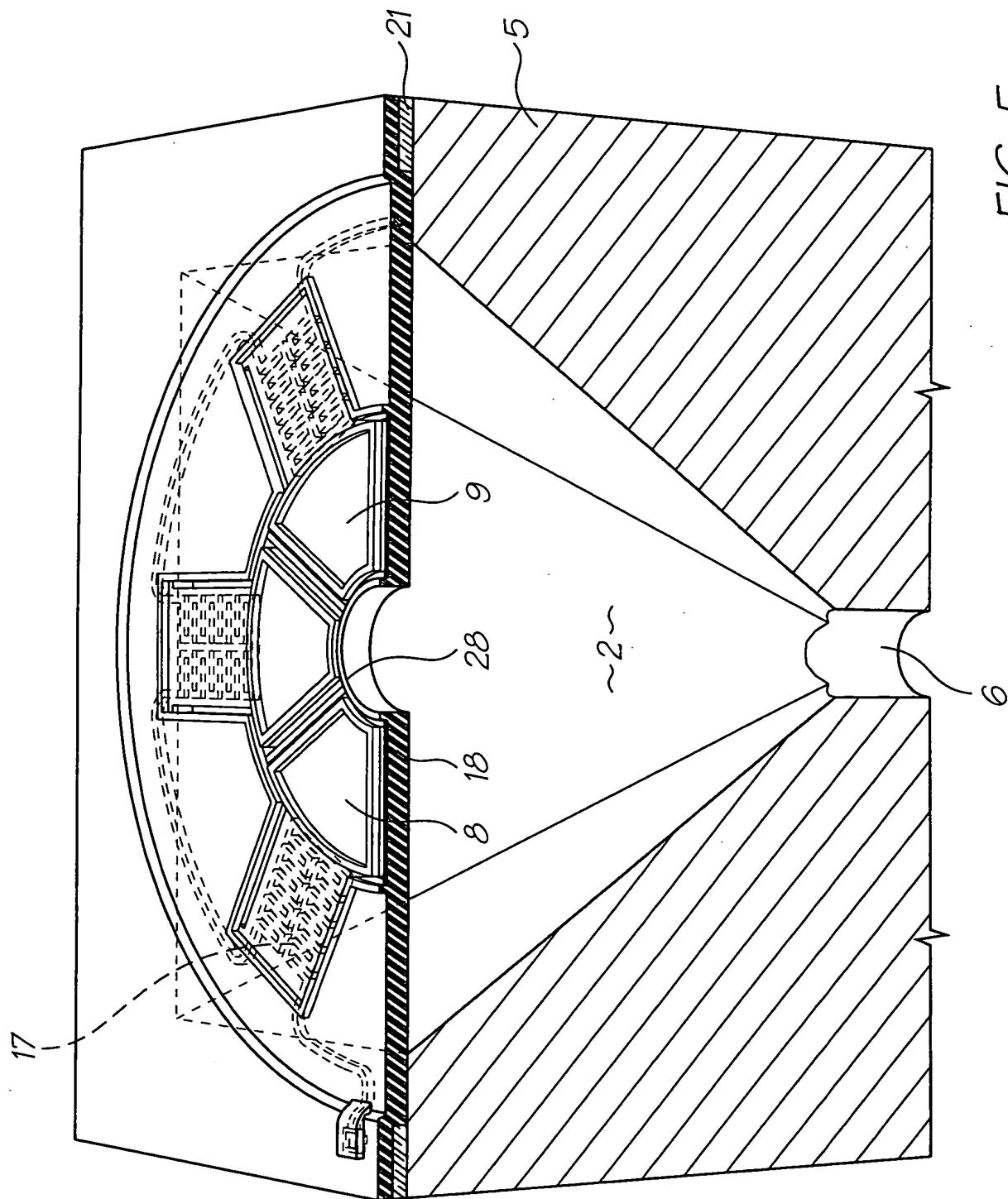


FIG. 4B



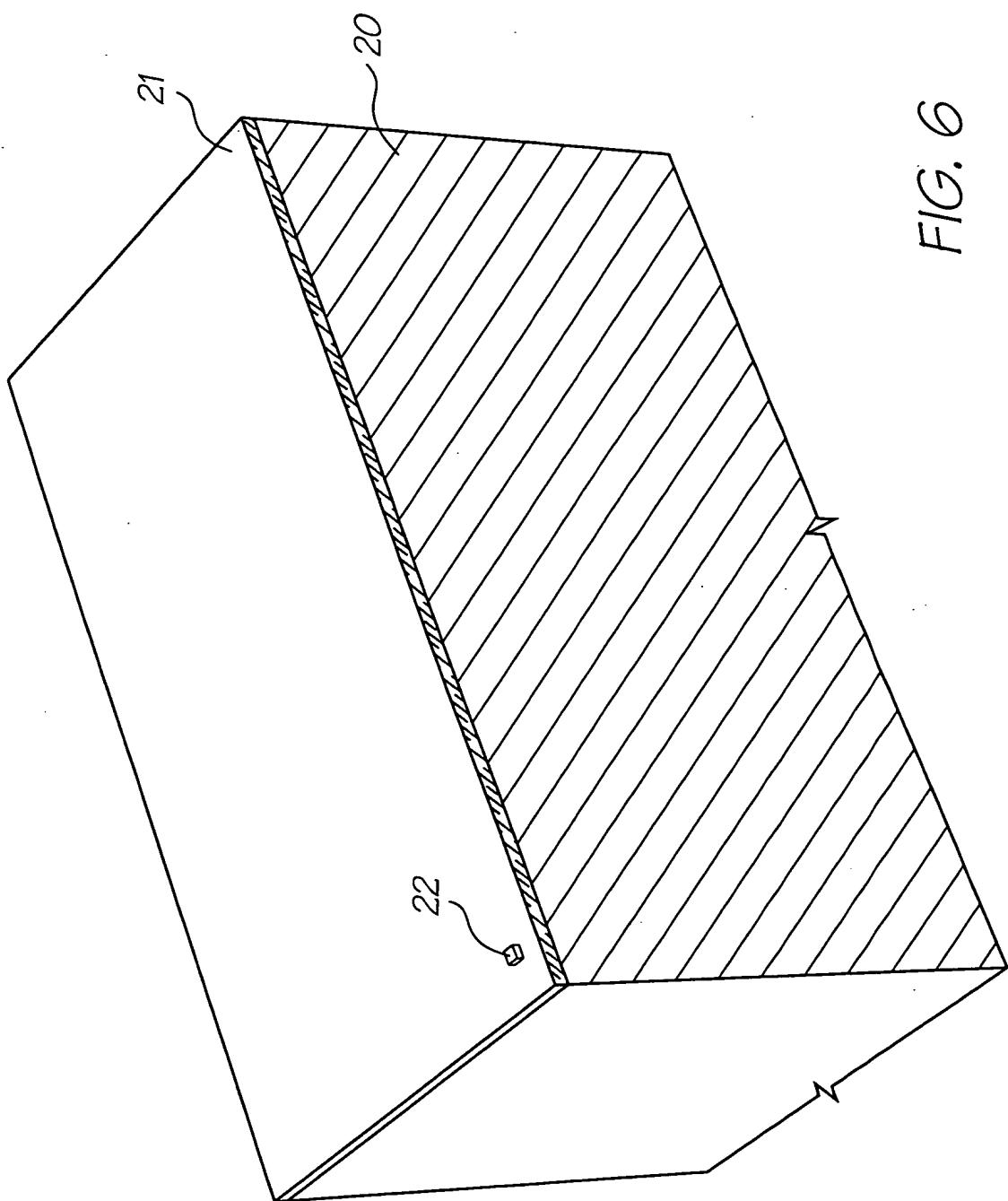


FIG. 6

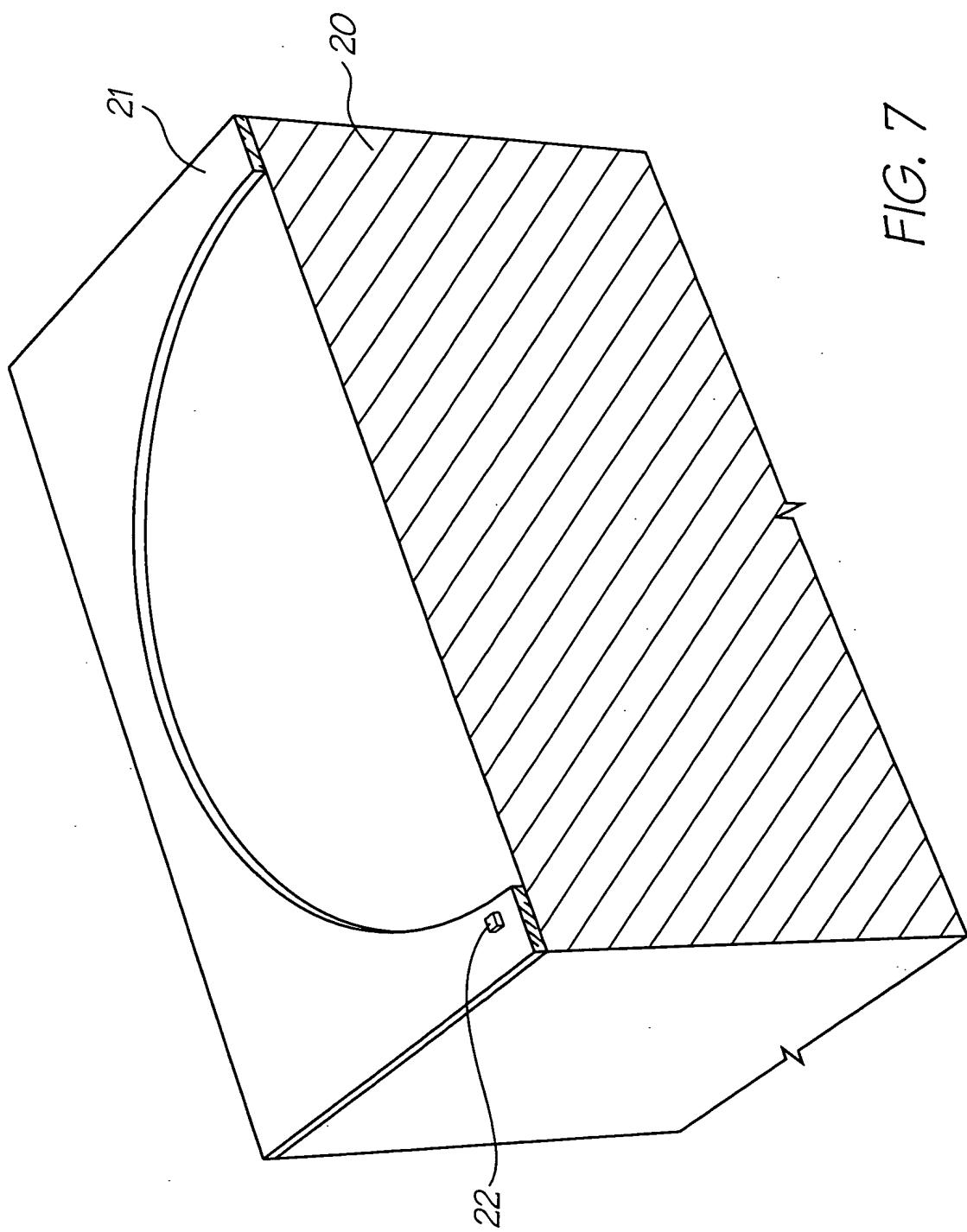


FIG. 7

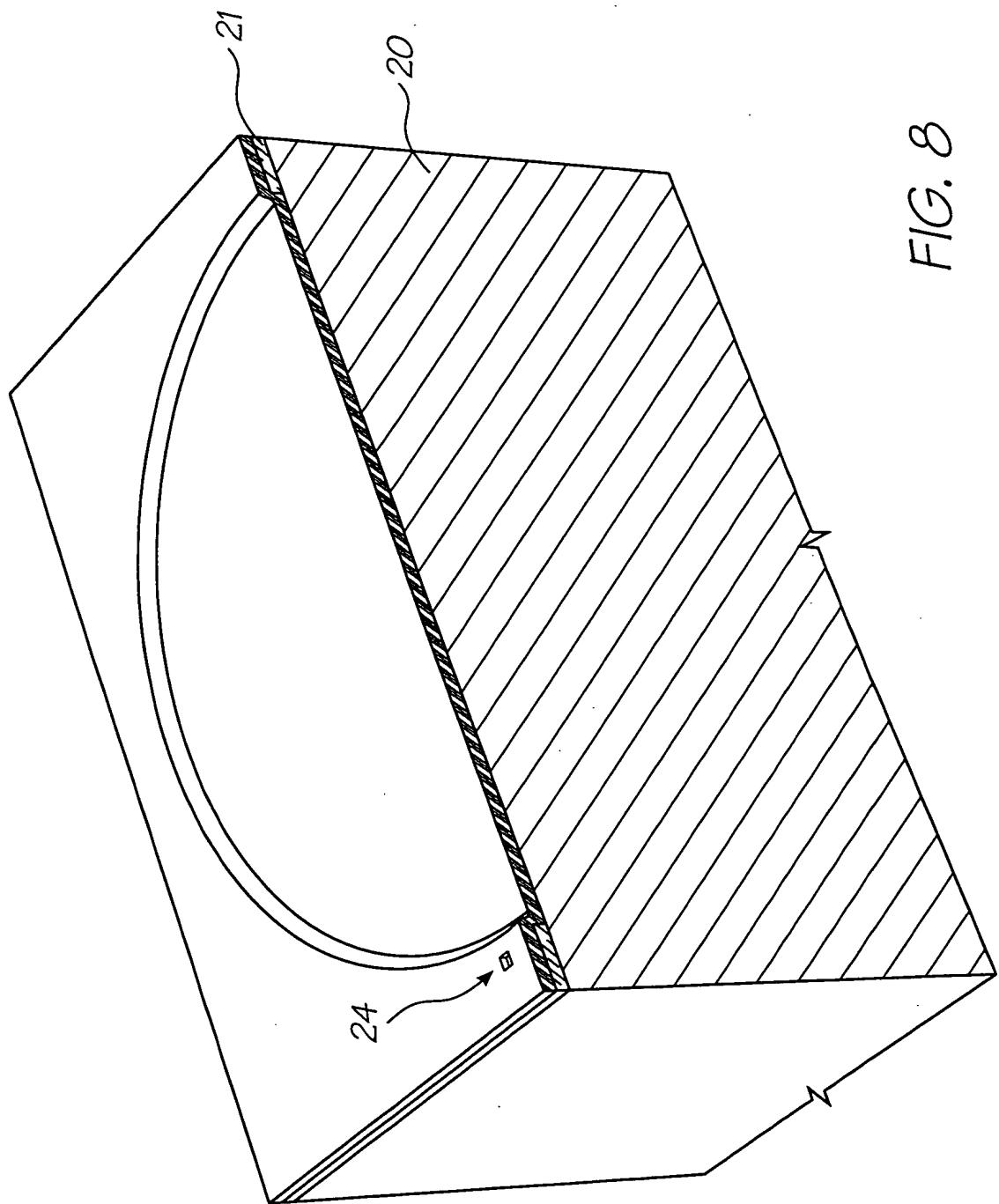


FIG. 8

FIG. 9

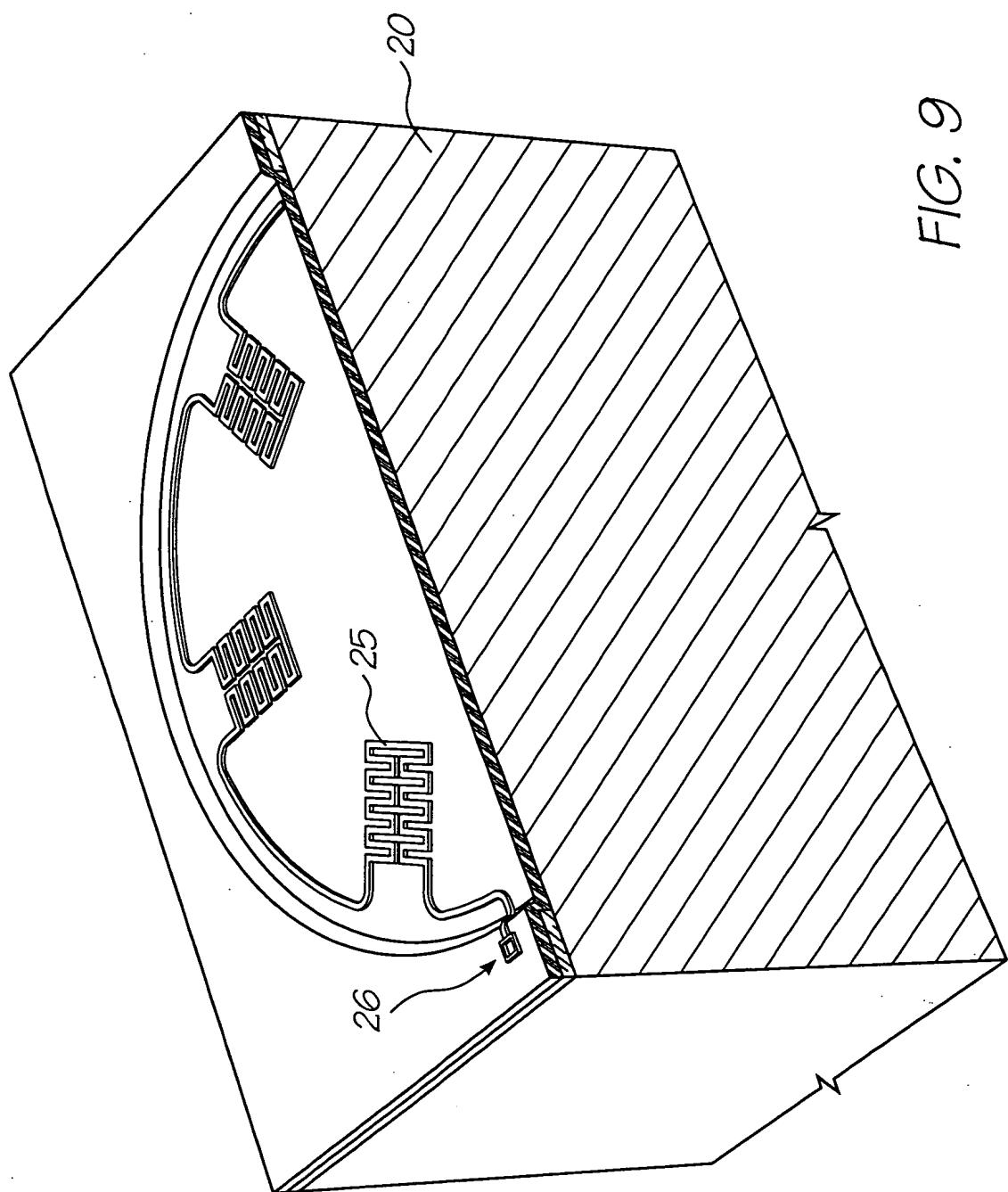
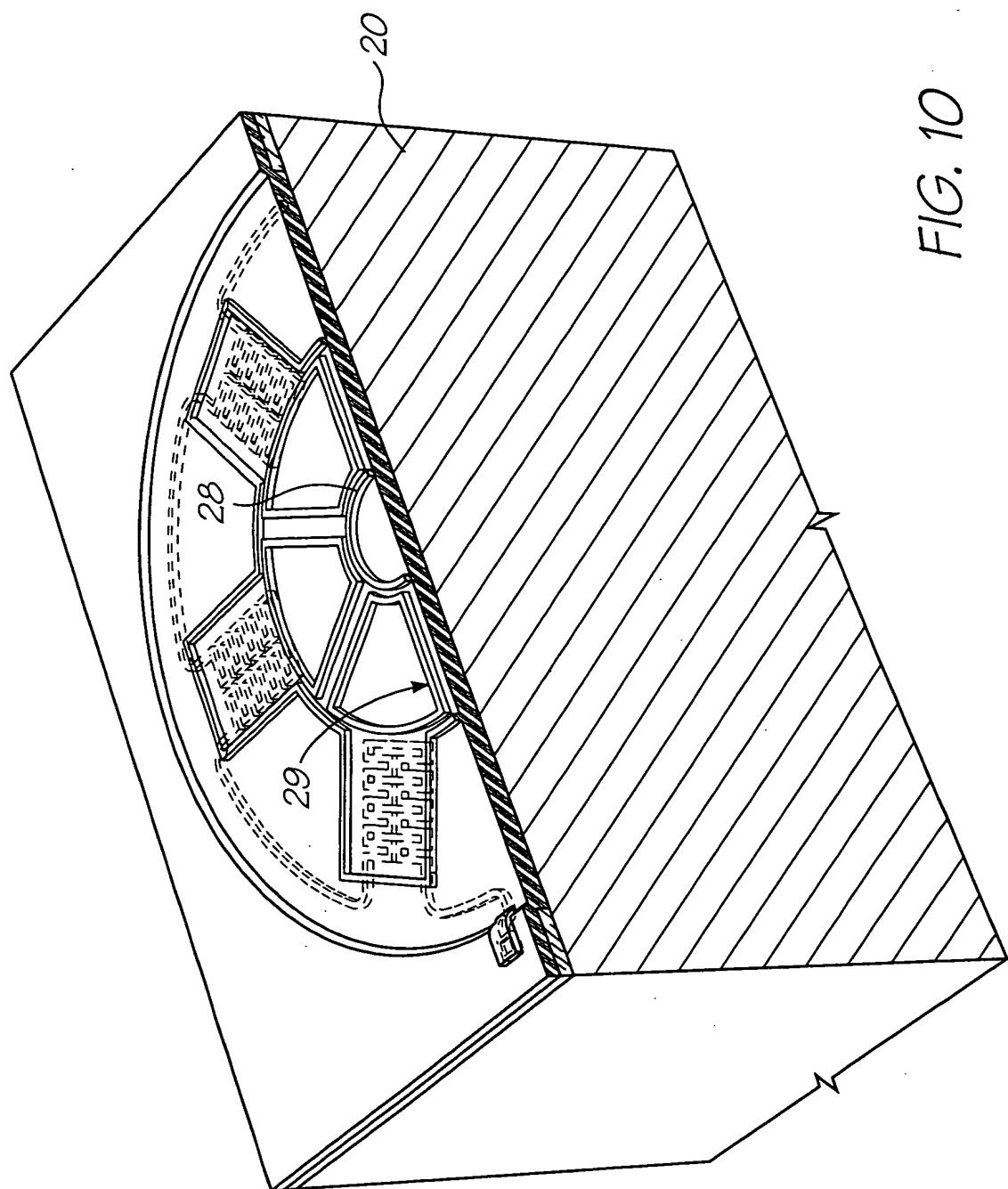
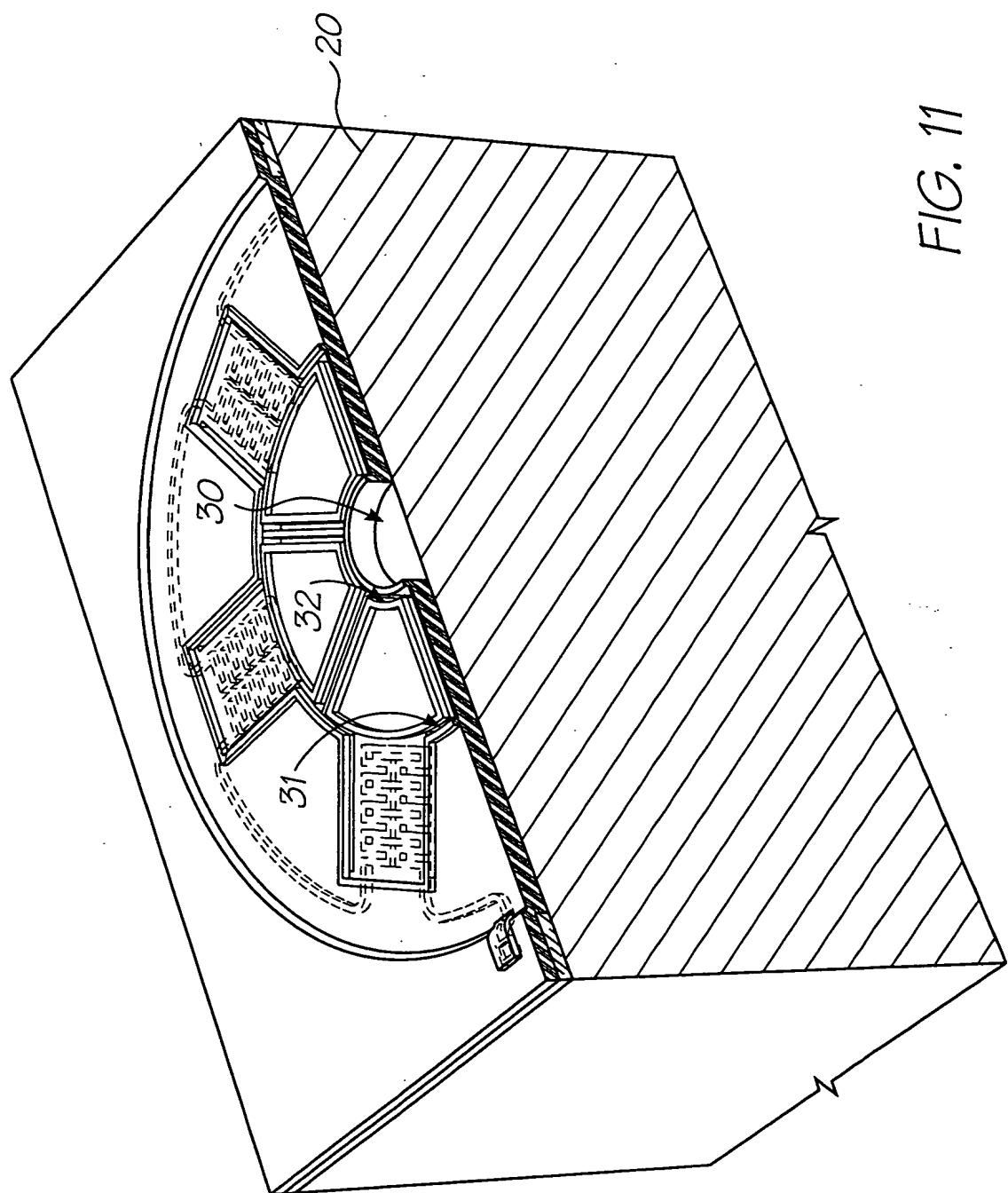
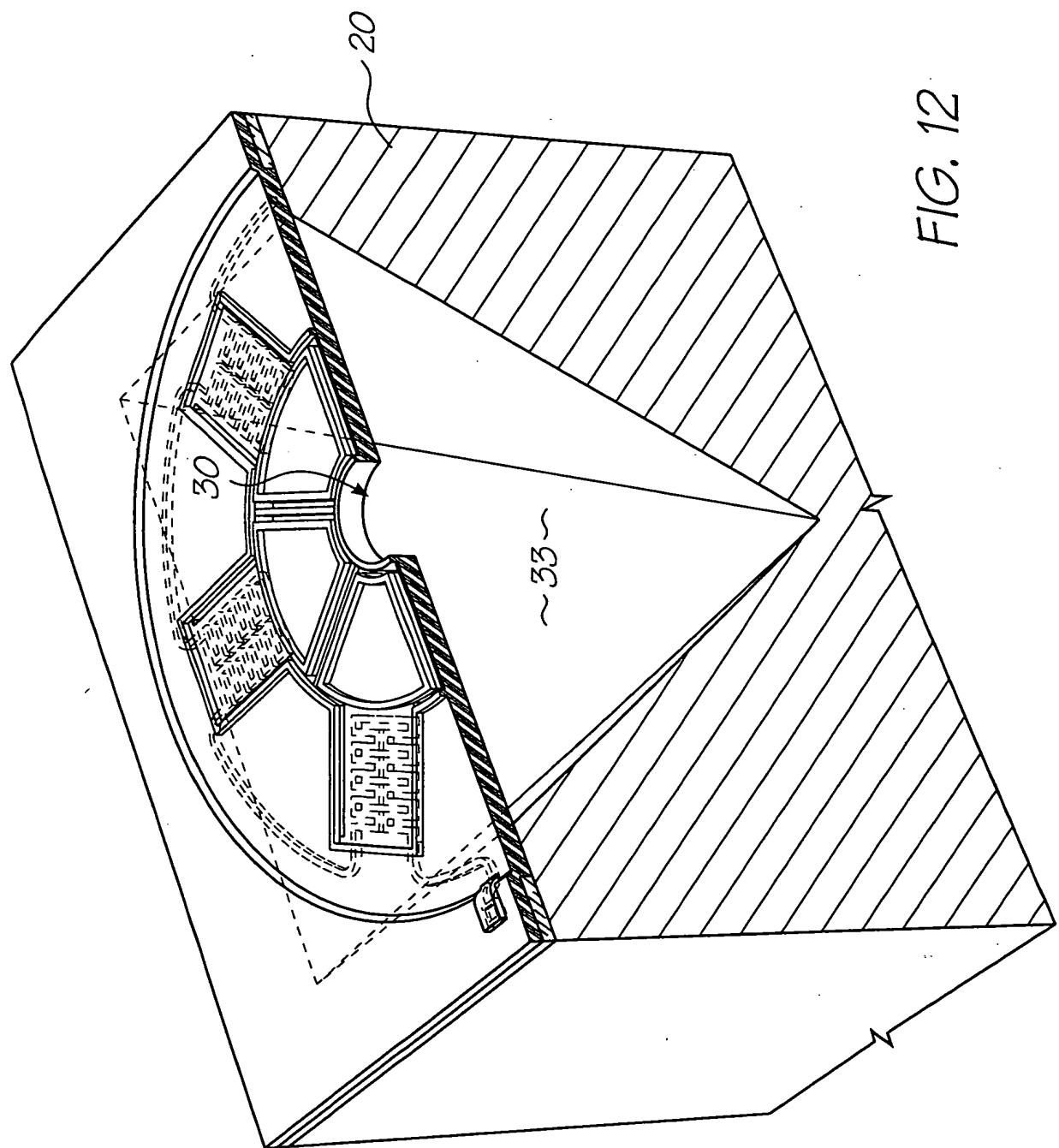
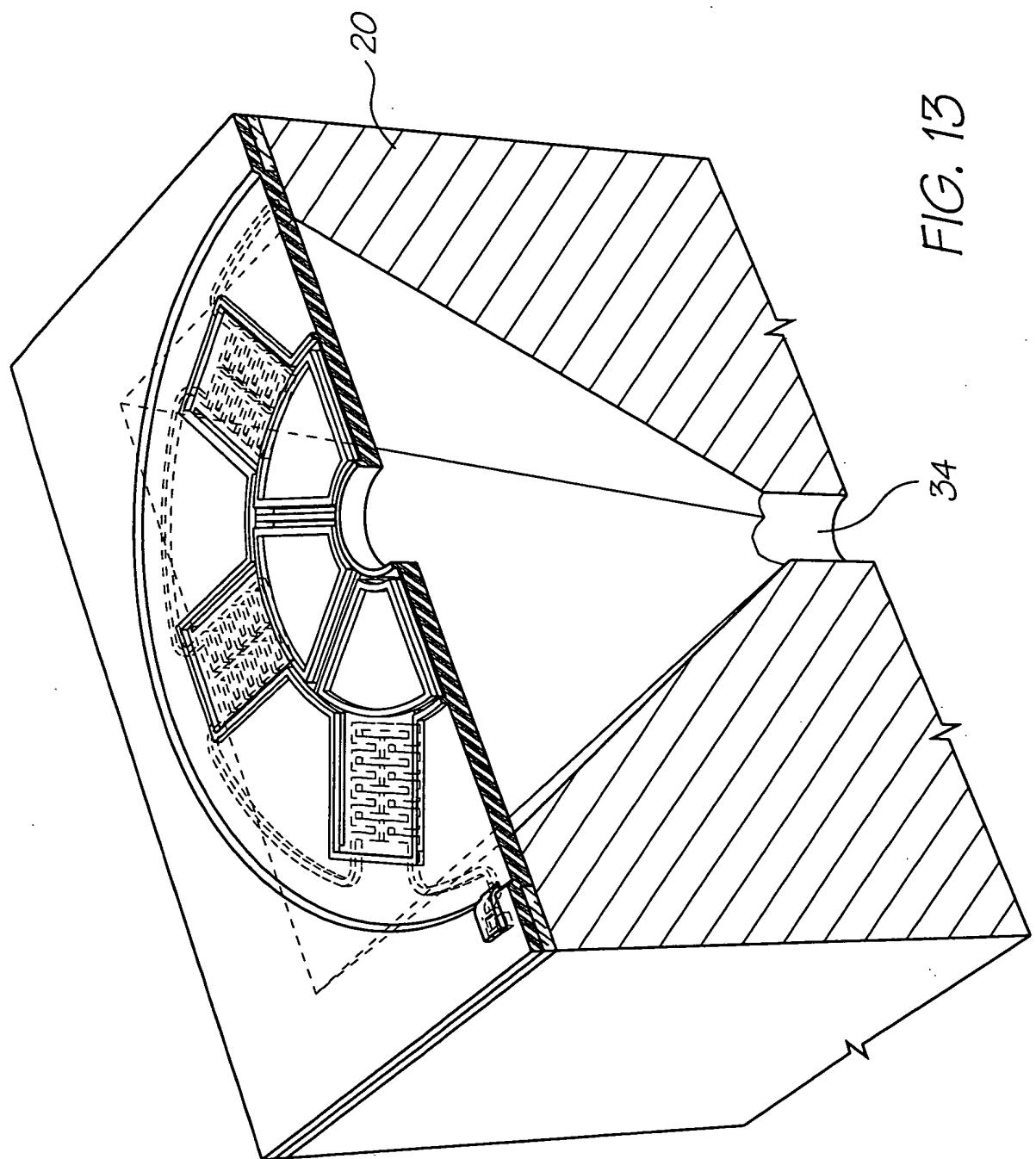


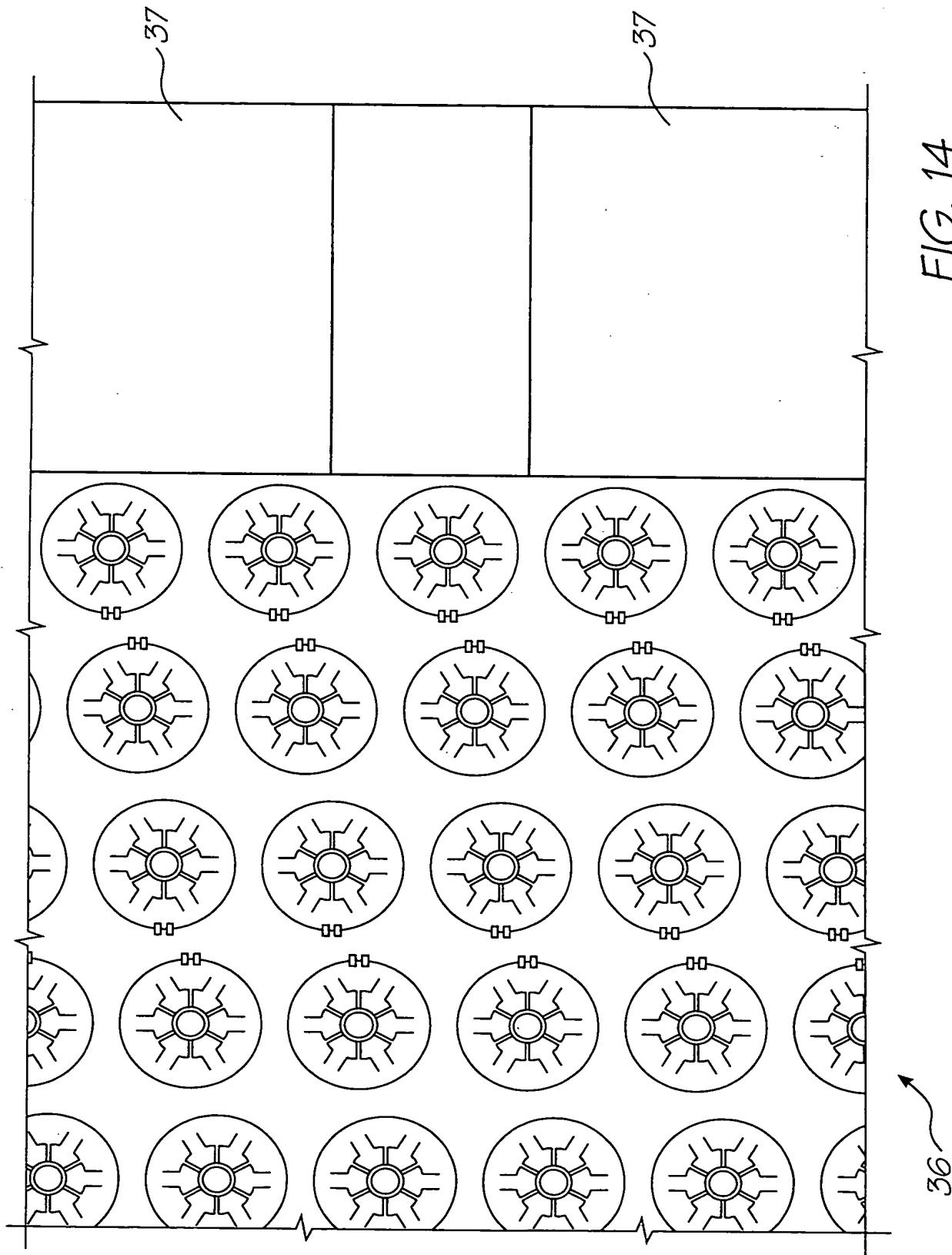
FIG. 10











	Silicon		Sacrificial material		Elastomer	
	Boron doped silicon		Cupronickel		Polyimide	
	Silicon nitride (Si_3N_4)		CoNiFe or NiFe		Indium tin oxide (ITO)	
	CMOS device region		Permanent magnet		PTFE	
	Aluminum		Polysilicon		Conductive PTFE	
	Glass (SiO_2)		Titanium Nitride (TiN)		Terfenol-D	
	Copper		Titanium boride (TiB_2)		Shape memory alloy	
	Gold		Adhesive		Tantalum	
			Resist			Ink

FIG. 15

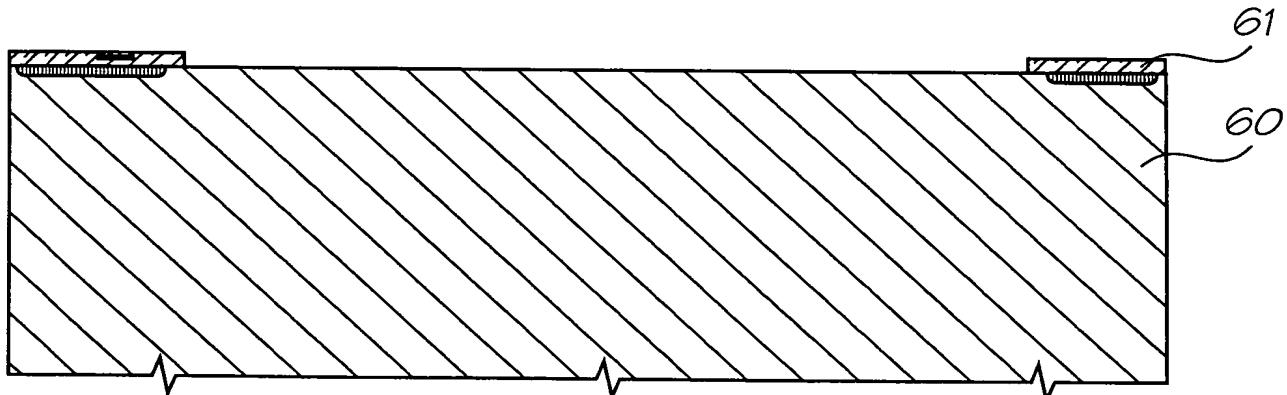


FIG. 16

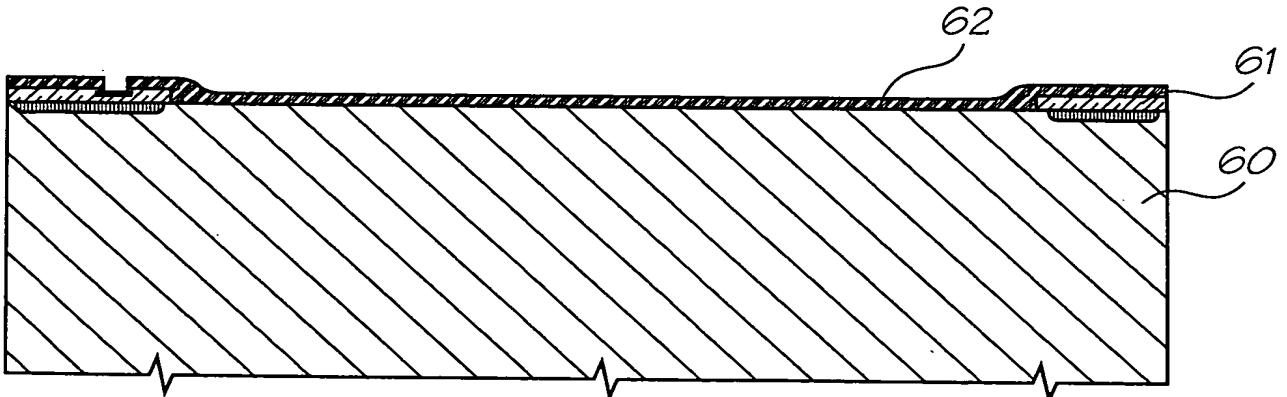


FIG. 17

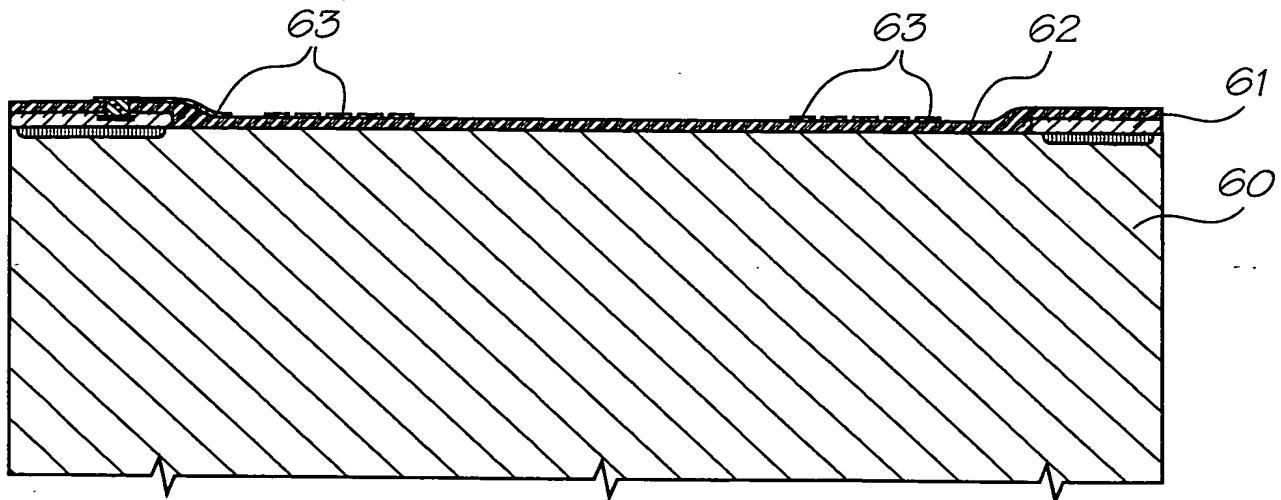


FIG. 18

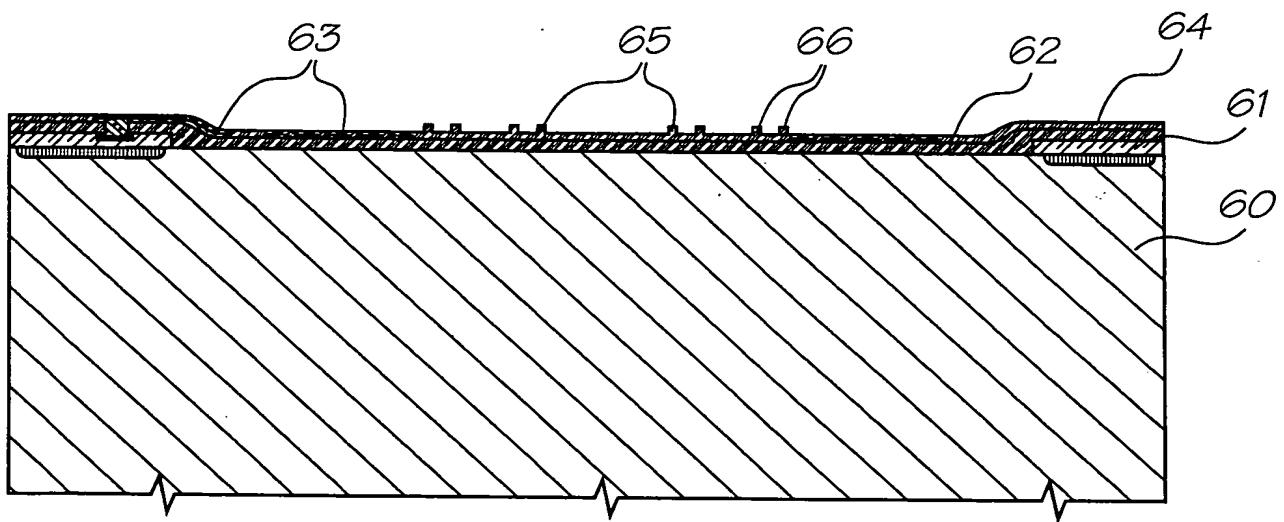


FIG. 19

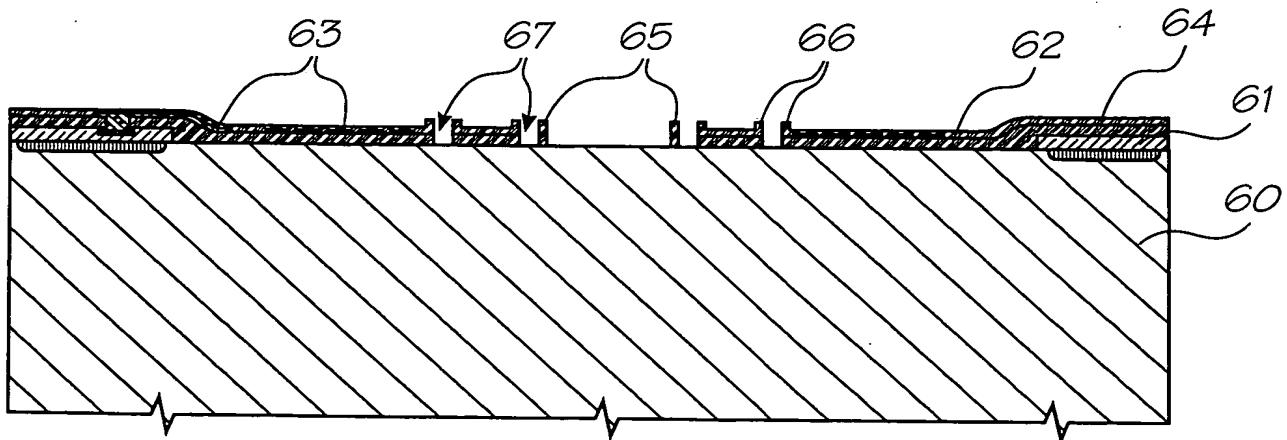


FIG. 20

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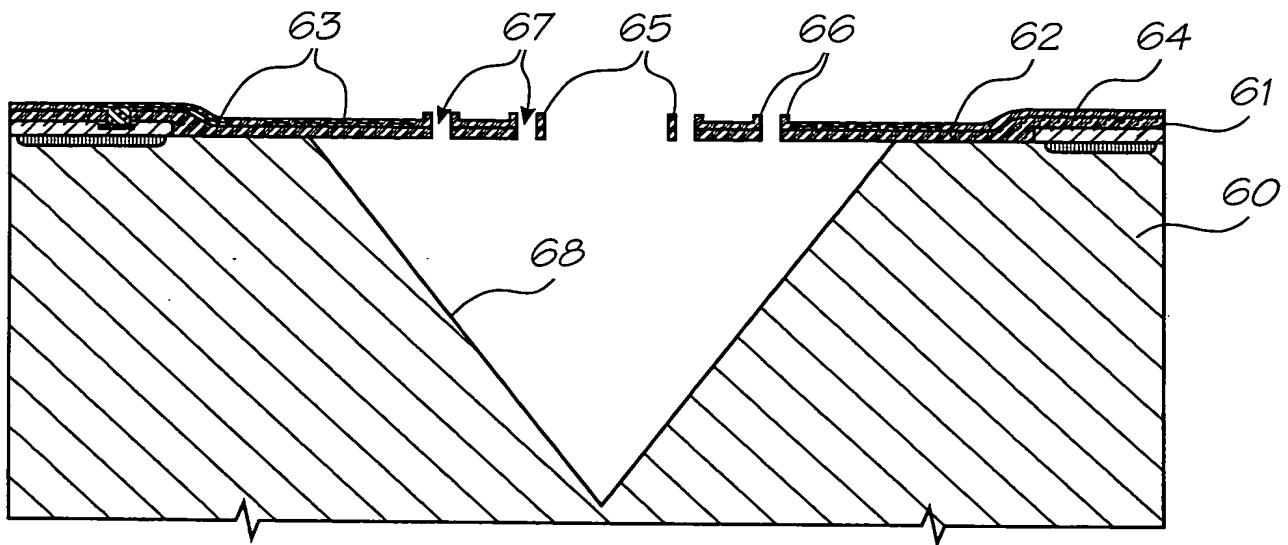


FIG. 21

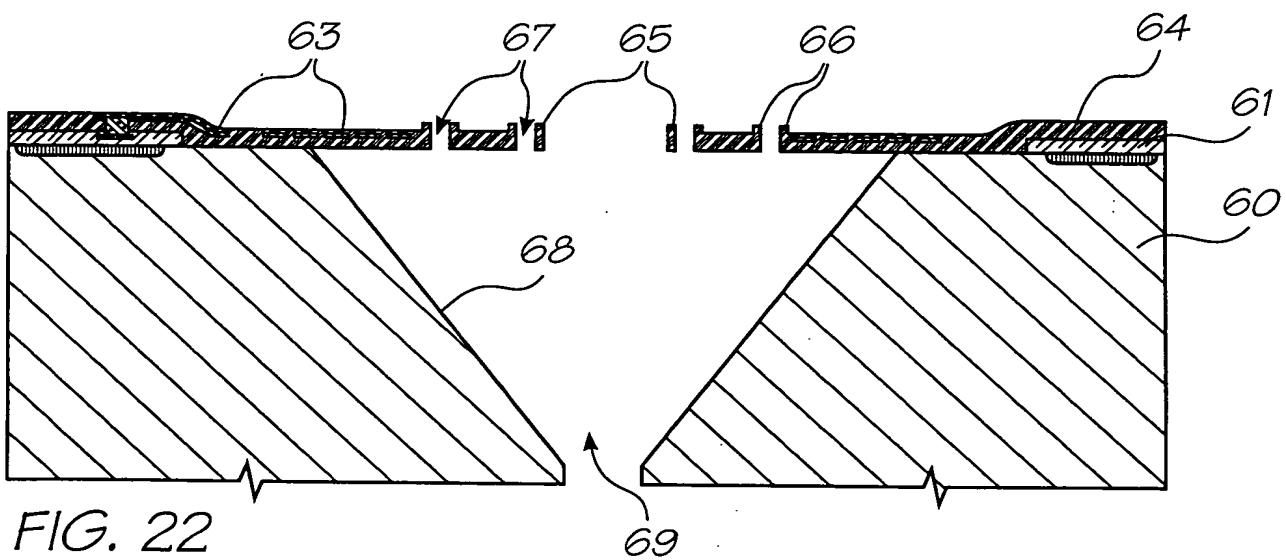


FIG. 22

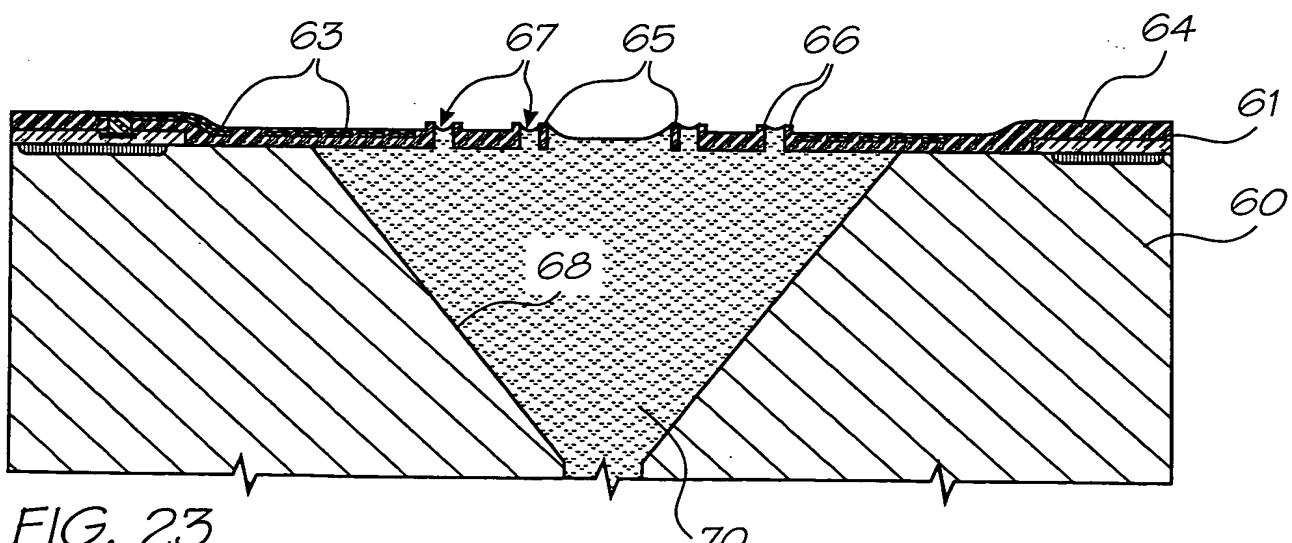


FIG. 23